

GB50XF120K

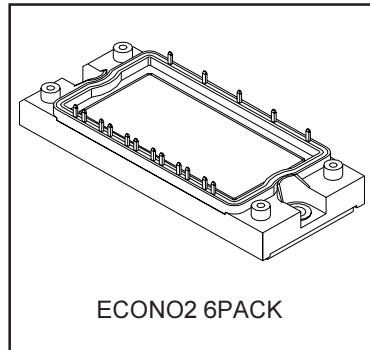
IGBT SIXPACK MODULE

Features

- Low V_{CE} (on) Non Punch Through IGBT Technology
- Low Diode VF
- 10μs Short Circuit Capability
- Square RBSOA
- HEXFRED Antiparallel Diode with Ultrasoft Reverse Recovery Characteristics
- Positive V_{CE} (on) Temperature Coefficient
- Ceramic DBC Substrate
- Low Stray Inductance Design

Benefits

- Benchmark Efficiency for Motor Control
- Rugged Transient Performance
- Low EMI, Requires Less Snubbing
- Direct Mounting to Heatsink
- PCB Solderable Terminals
- Low Junction to Case Thermal Resistance
- UL Approved E78996 

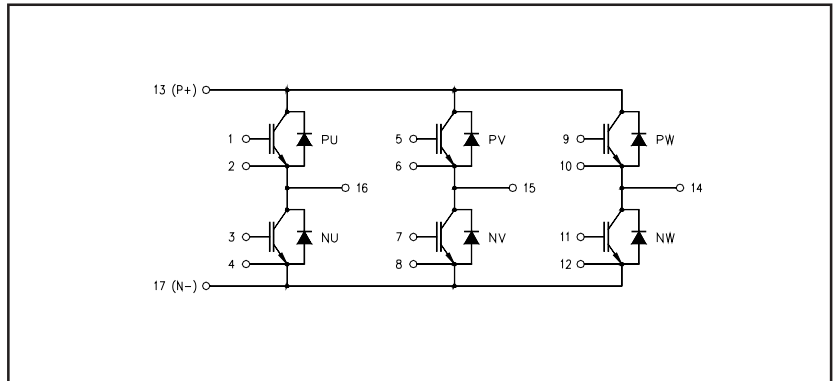


$$V_{CES} = 1200V$$

$$I_C = 50A @ T_C=80^{\circ}C$$

$$t_{sc} > 10\mu s @ T_J=150^{\circ}C$$

$$V_{CE(on)} \text{ typ.} = 2.45V$$



Absolute Maximum Ratings

	Parameter	Max.	Units
V _{CES}	Collector-to-Emitter Voltage	1200	V
I _C @ T _C =25°C	Continuous Collector Current	75	A
I _C @ T _C =80°C	Continuous Collector Current	50	
I _{CM}	Pulsed Collector Current (Ref. Fig. C.T.5)	150	
I _{LM}	Clamped Inductive Load Current	150	
I _F @ T _C =25°C	Diode Continuous Forward Current	75	
I _F @ T _C =80°C	Diode Continuous Forward Current	50	
I _{FM}	Pulsed Diode Maximum Forward Current	150	
V _{GE}	Gate-to-Emitter Voltage	±20	V
P _D @ T _C =25°C	Maximum Power Dissipation (IGBT and Diode)	329	W
P _D @ T _C =80°C	Maximum Power Dissipation (IGBT and Diode)	184	
T _J	Maximum Operating Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-40 to +125	
V _{ISOL}	Isolation Voltage	AC 2500 (MIN)	V

Thermal and Mechanical Characteristics

	Parameter	Min	Typical	Maximum	Units
R _{θJC} (IGBT)	Junction-to-Case IGBT	-	-	0.38	°C/W
R _{θJC} (Diode)	Junction-to-Case Diode	-	-	0.70	
R _{θCS} (Module)	Case-to-Sink, flat, greased surface	-	0.05	-	
	Mounting Torque (M5)	2.7	-	3.3	N*m
	Weight	-	170	-	g

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$BV_{(CES)}$	Collector-to-Emitter Breakdown Voltage	1200	-	-	V	$V_{GE} = 0$ $I_C = 500\mu\text{A}$
$\Delta V_{(BR)CES}/\Delta T_J$	Temp. Coefficient of Breakdown Voltage	-	0.31	-	V/ $^\circ\text{C}$	$V_{GE} = 0$ $I_C = 1\text{mA}$ ($25^\circ\text{C} - 125^\circ\text{C}$)
$V_{CE(ON)}$	Collector-to-Emitter Voltage	-	2.45	2.65	V	$I_C = 50\text{A}$ $V_{GE} = 15\text{V}$
		-	2.85	3.15		$I_C = 75\text{A}$ $V_{GE} = 15\text{V}$
		-	2.85	-		$I_C = 50\text{A}$ $V_{GE} = 15\text{V}$ $T_J = 125^\circ\text{C}$
		-	3.45	-		$I_C = 75\text{A}$ $V_{GE} = 15\text{V}$ $T_J = 125^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	4.0	4.9	6.0		$V_{CE} = V_{GE}$ $I_C = 250\mu\text{A}$
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	-	-12	-	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}$ $I_C = 1\text{mA}$ ($25^\circ\text{C} - 125^\circ\text{C}$)
I_{CES}	Zero Gate Voltage Collector Current	-	-	100	μA	$V_{GE} = 0$ $V_{CE} = 1200\text{V}$
		-	1000	-		$V_{GE} = 0$ $V_{CE} = 1200\text{V}$ $T_J = 125^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	-	1.95	2.25	V	$I_F = 50\text{A}$
		-	2.20	2.60		$I_F = 75\text{A}$
		-	2.05	-		$I_F = 50\text{A}$ $T_J = 125^\circ\text{C}$
		-	2.40	-		$I_F = 75\text{A}$ $T_J = 125^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	-	-	± 200	nA	$V_{GE} = \pm 20\text{V}$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_G	Total Gate Charge (turn-on)	-	355	535	nC	$I_C = 50\text{A}$
Q_{GE}	Gate-to-Emitter Charge (turn-on)	-	35	55		$V_{CC} = 600\text{A}$
Q_{GC}	Gate-to-Collector Charge (turn-on)	-	165	250		$V_{GE} = 15\text{V}$
E_{ON}	Turn-On Switching Loss	-	3600	4635	μJ	$I_C = 50\text{A}$ $V_{CC} = 600\text{V}$
E_{OFF}	Turn-Off Switching Loss	-	3740	4780		$V_{GE} = 15\text{V}$ $R_G = 10\Omega$ $L = 400\mu\text{H}$
E_{TOT}	Total Switching Loss	-	7340	9415		$T_J = 25^\circ\text{C}$ ①
E_{ON}	Turn-On Switching Loss	-	5050	7100	μJ	$I_C = 50\text{A}$ $V_{CC} = 600\text{V}$
E_{OFF}	Turn-Off Switching Loss	-	5525	7750		$V_{GE} = 15\text{V}$ $R_G = 10\Omega$ $L = 400\mu\text{H}$
E_{TOT}	Total Switching Loss	-	10575	14850		$T_J = 125^\circ\text{C}$ ①
$t_{d(on)}$	Turn-On delay time	-	60	80	ns	$I_C = 50\text{A}$ $V_{CC} = 600\text{V}$
t_r	Risetime	-	40	60		$V_{GE} = 15\text{V}$ $R_G = 10\Omega$ $L = 400\mu\text{H}$
$t_{d(off)}$	Turn-Off delay time	-	570	665		$T_J = 125^\circ\text{C}$
t_f	Falltime	-	205	270		
C_{ies}	Input Capacitance	-	4945	-	pF	$V_{GE} = 0$
C_{oes}	Output Capacitance	-	885	-		$V_{CC} = 30\text{V}$
C_{res}	Reverse Transfer Capacitance	-	100	-		$f = 1\text{Mhz}$
RBSOA	Reverse Bias Safe Operating Area	FULLSQUARE				$T_J = 150^\circ\text{C}$ $I_C = 150\text{A}$ $R_G = 10\Omega$ $V_{GE} = 15\text{V to } 0$
SCSOA	Short Circuit Safe Operating Area	10	-	-	μs	$T_J = 150^\circ\text{C}$ $V_{CC} = 900\text{V}$ $V_P = 1200\text{V}$ $R_G = 10\Omega$ $V_{GE} = 15\text{V to } 0$
I_{rr}	Diode Peak Rev. Recovery Current	-	87	-	A	$T_J = 125^\circ\text{C}$ $V_{CC} = 600\text{V}$ $I_F = 50\text{A}$ $L = 400\mu\text{H}$ $V_{GE} = 15\text{V}$ $R_G = 10\Omega$

① Energy losses include "tail" and diode reverse recovery.

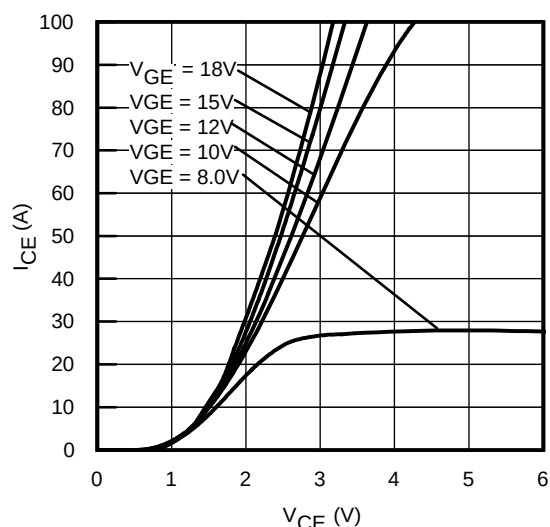


Fig. 1 - Typ. IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p = 80\mu\text{s}$

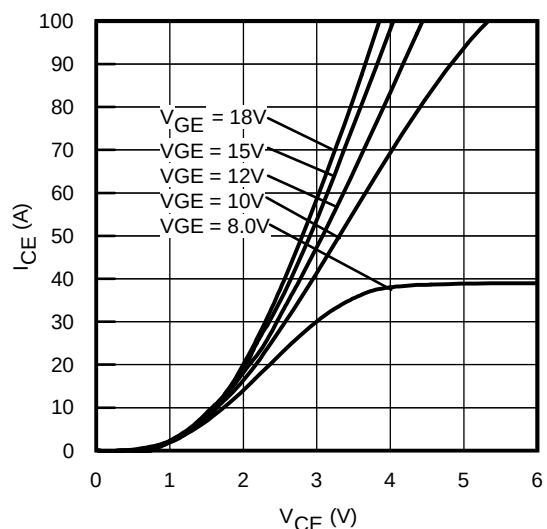


Fig. 2 - Typ. IGBT Output Characteristics
 $T_J = 125^\circ\text{C}$; $t_p = 80\mu\text{s}$

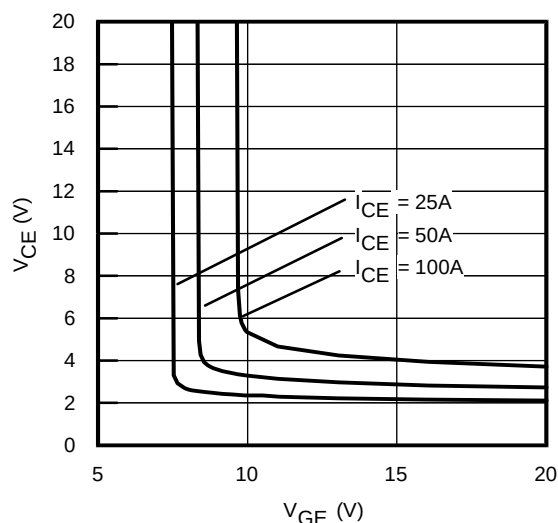


Fig. 3 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

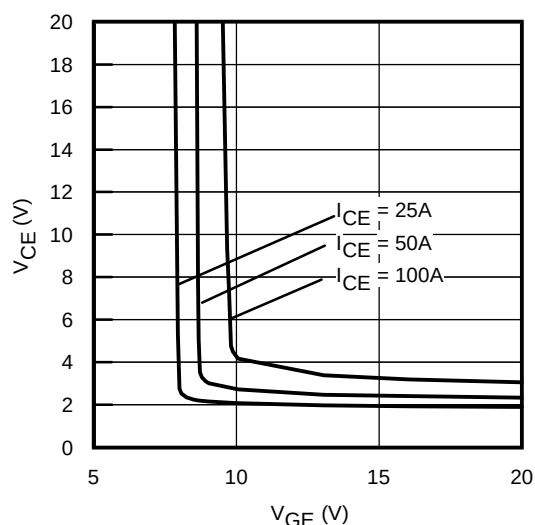


Fig. 4 - Typical V_{CE} vs. V_{GE}
 $T_J = 125^\circ\text{C}$

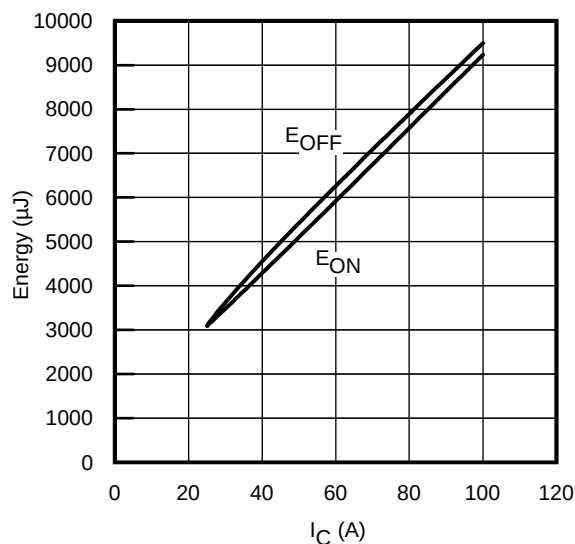


Fig. 5 - Typ. Energy Loss vs. I_C
 $T_J = 125^\circ\text{C}$; $L = 400\mu\text{H}$; $V_{CE} = 600\text{V}$
 $R_G = 10\Omega$; $V_{GE} = 15\text{V}$

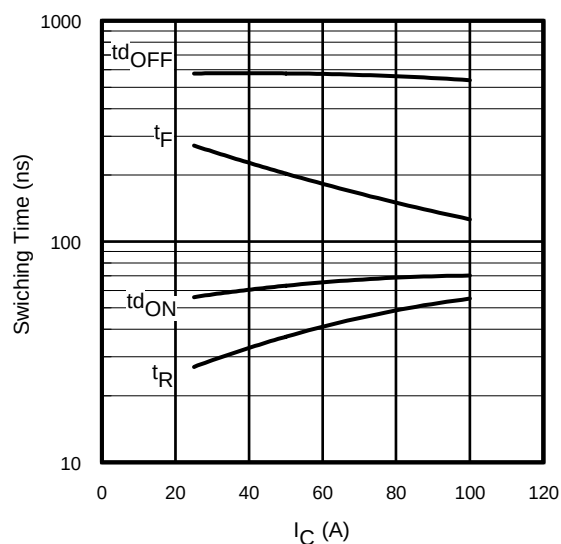


Fig. 6 - Typ. Switching Time vs. I_C
 $T_J = 125^\circ\text{C}$; $L = 400\mu\text{H}$; $V_{CE} = 600\text{V}$
 $R_G = 10\Omega$; $V_{GE} = 15\text{V}$

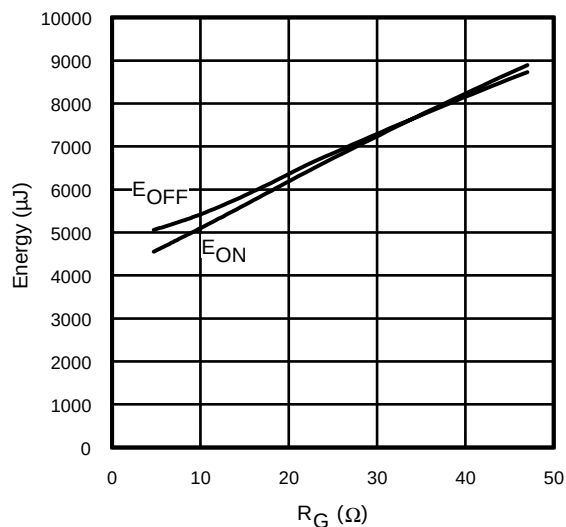


Fig. 7 - Typ. Energy Loss vs. R_G
 $T_J = 125^\circ\text{C}$; $L=400\mu\text{H}$; $V_{CE}=600\text{V}$
 $I_{CE}=50\text{A}$; $V_{GE}=15\text{V}$

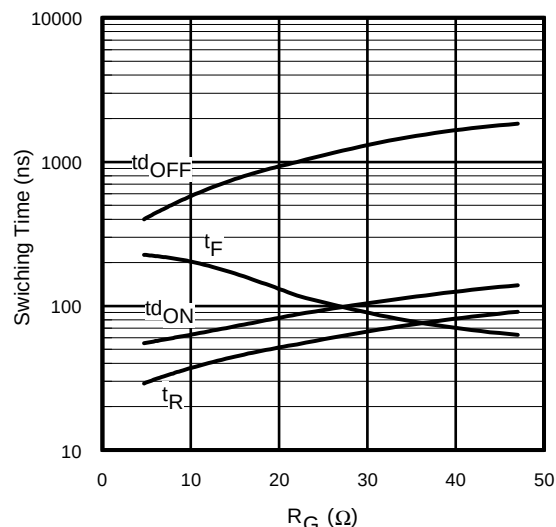


Fig. 8 - Typ. Switching Time vs. R_G
 $T_J = 125^\circ\text{C}$; $L=400\mu\text{H}$; $V_{CE}=600\text{V}$
 $I_{CE}=50\text{A}$; $V_{GE}=15\text{V}$

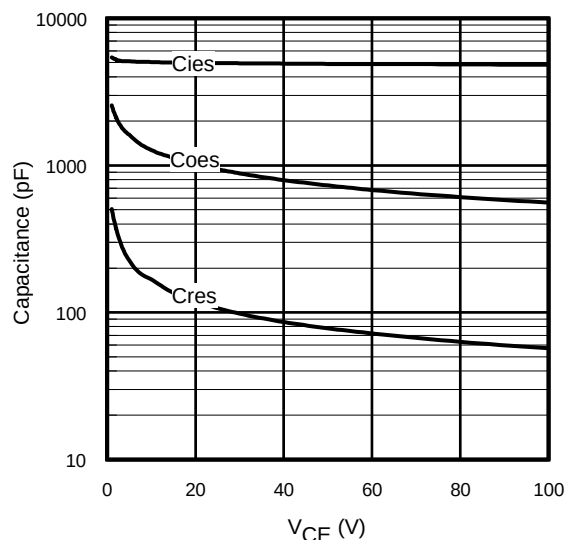


Fig. 9 - Typ. Capacitance vs. V_{CE}
 $V_{GE}=0\text{V}$; $f=1\text{MHz}$

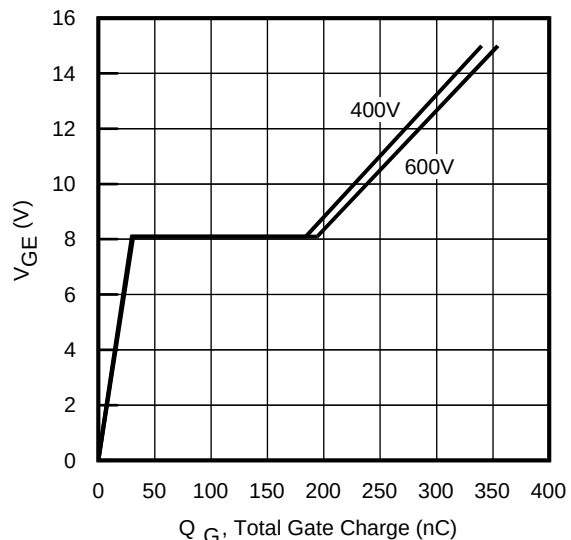


Fig. 10 - Typical Gate Charge vs. V_{GE}
 $I_{CE}=50\text{A}$; $L=600\mu\text{H}$

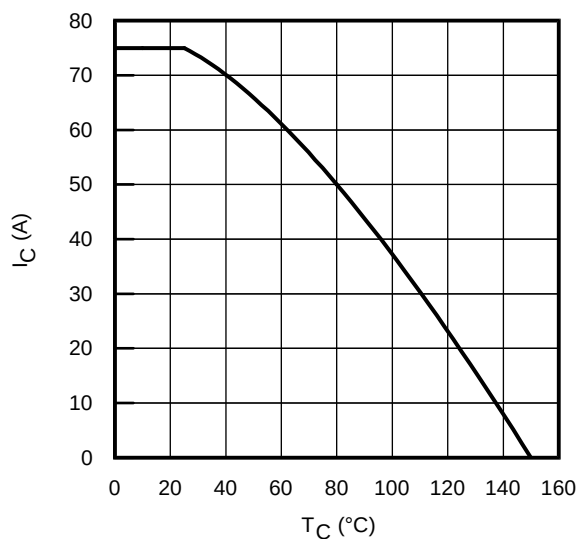


Fig. 11 - Maximum DC Collector Current vs. Case Temperature

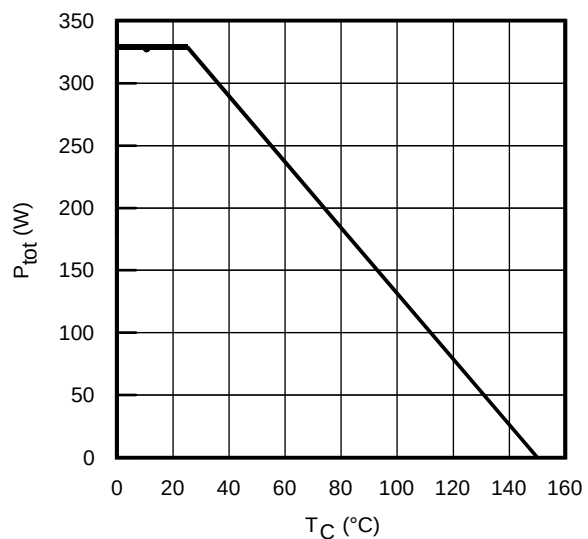


Fig. 12 - Power Dissipation vs. Case Temperature

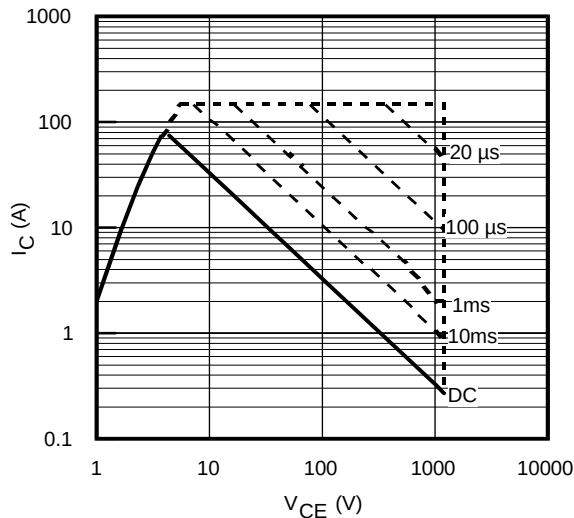


Fig. 13 - Forward SOA
 $T_C = 25^\circ\text{C}; T_J \leq 150^\circ\text{C}$

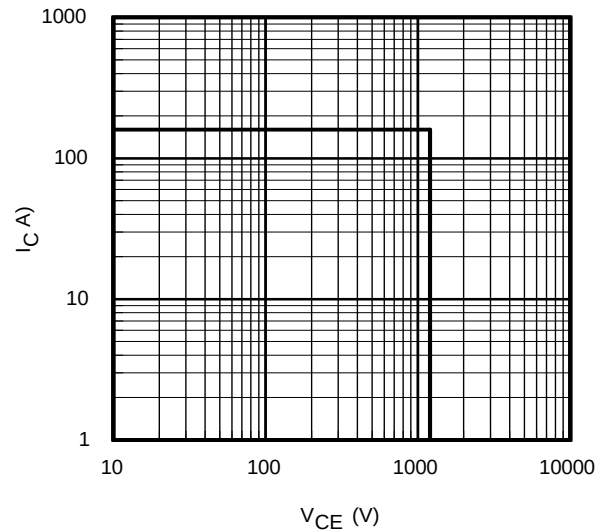


Fig. 14 - Reverse Bias SOA
 $T_J = 150^\circ\text{C}; V_{GE} = 15\text{V}$

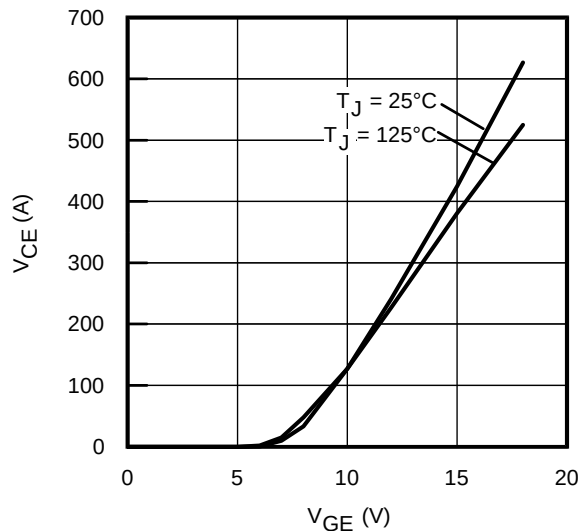


Fig. 15 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}; t_p = 10\mu\text{s}$

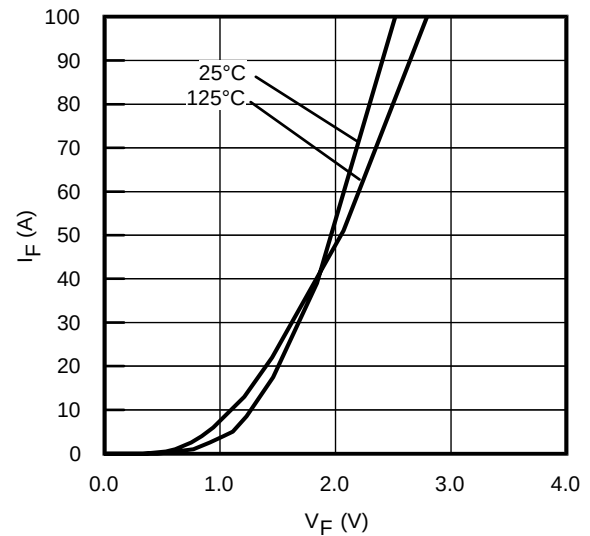


Fig. 16 - Typ. Diode Forward Characteristics
 $t_p = 80\mu\text{s}$

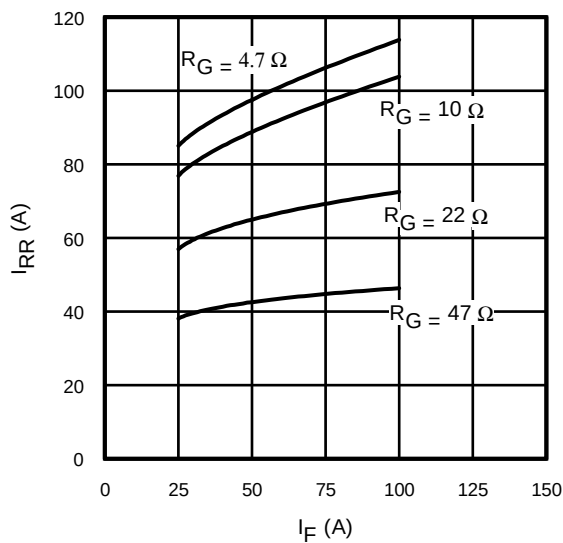


Fig. 17 - Typical Diode I_{RR} vs. I_F
 $T_J = 125^\circ\text{C}$

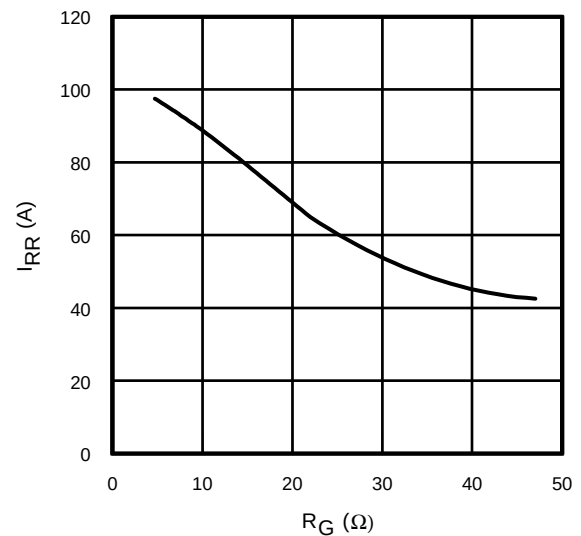


Fig. 18 - Typical Diode I_{RR} vs. R_G
 $T_J = 125^\circ\text{C}; I_F = 50\text{A}$

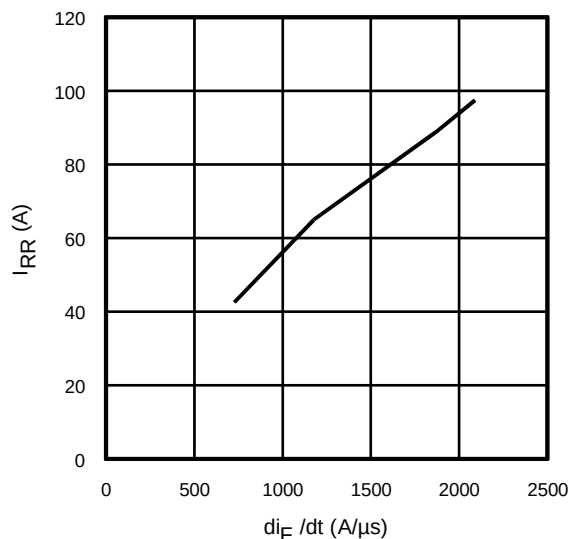


Fig. 19- Typical Diode I_{RR} vs. di_F/dt ; $V_{CC} = 600V$;
 $V_{GE} = 15V$; $I_{CE} = 50A$; $T_J = 125^\circ C$

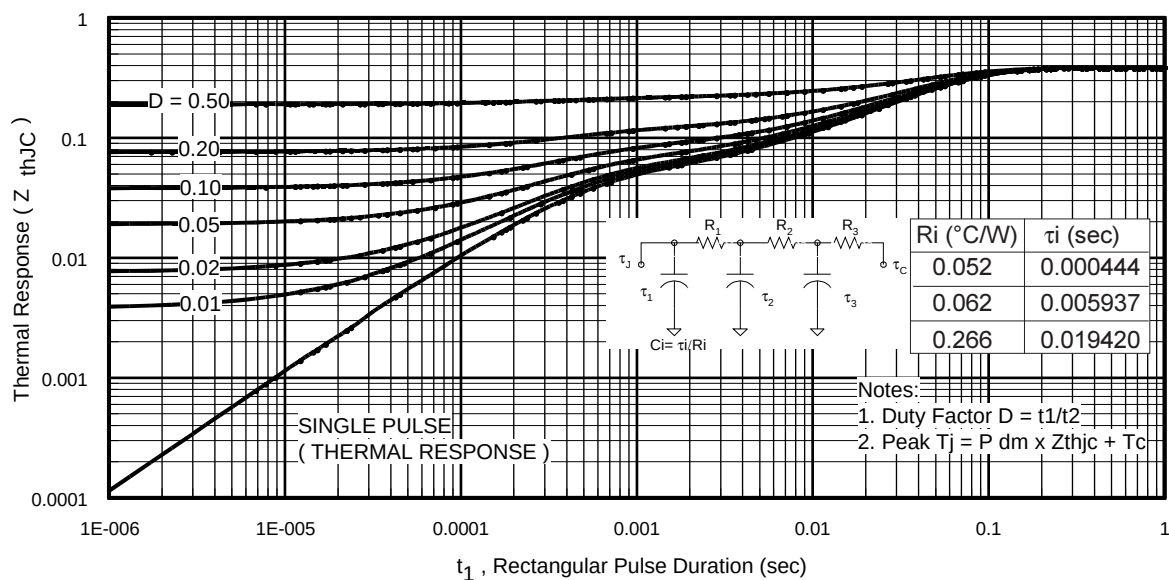


Fig 20. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

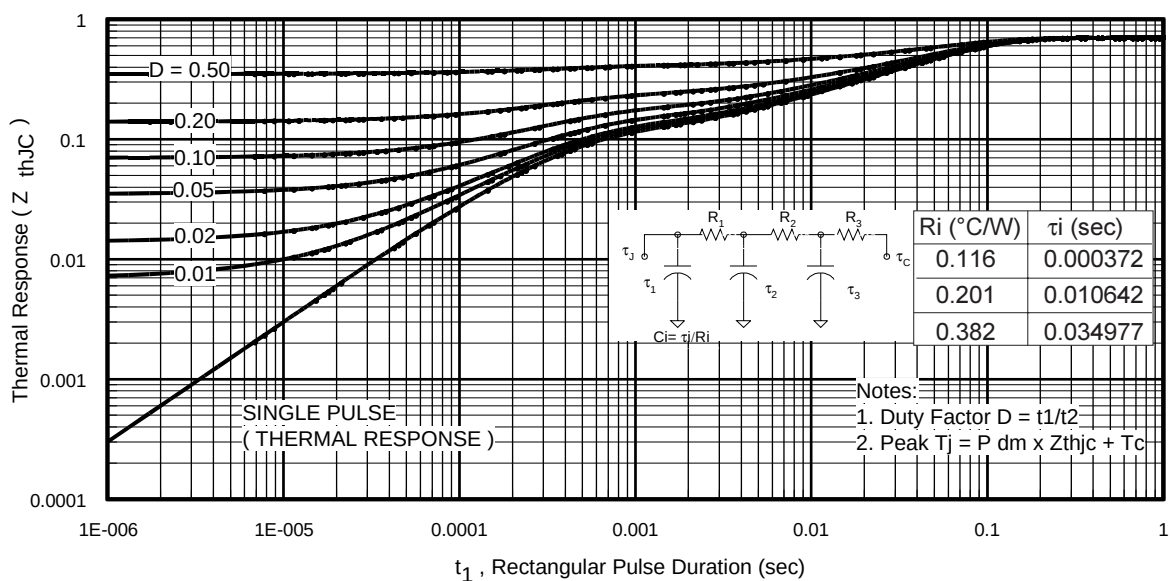


Fig 21. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

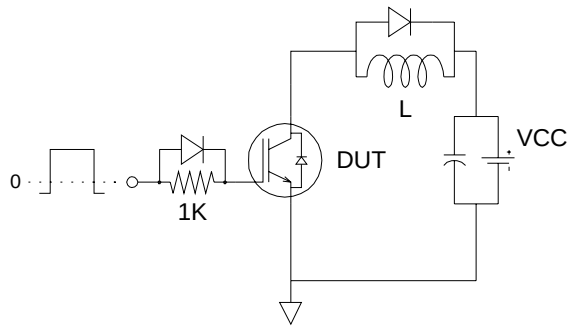


Fig.C.T.1 - Gate Charge Circuit (turn-off)

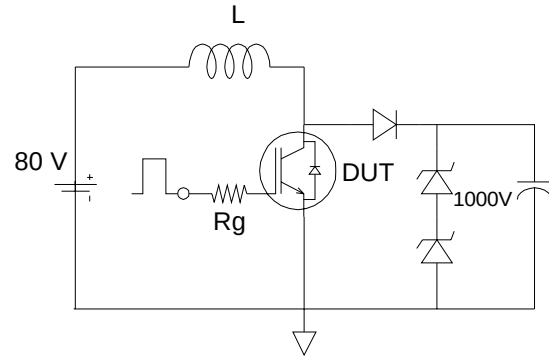


Fig.C.T.2 - RBSOA Circuit

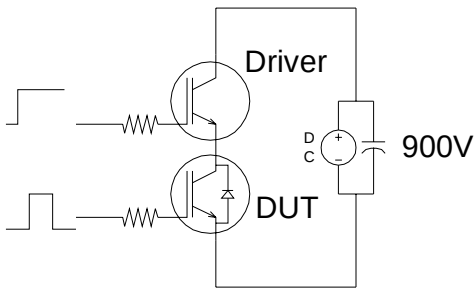


Fig.C.T.3 - S.C. SOA Circuit

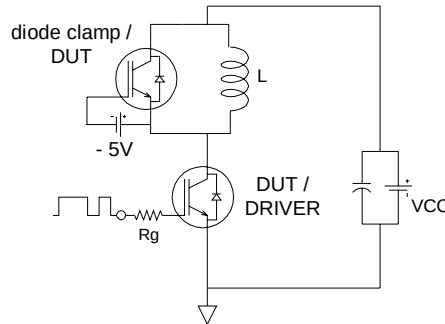


Fig.C.T.4 - Switching Loss Circuit

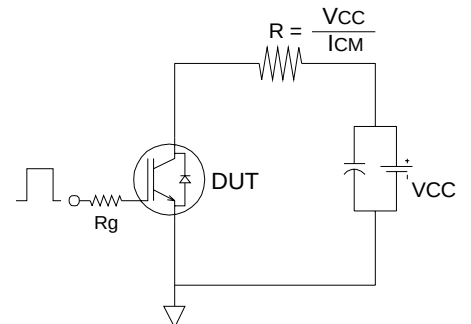


Fig.C.T.5 - Resistive Load Circuit

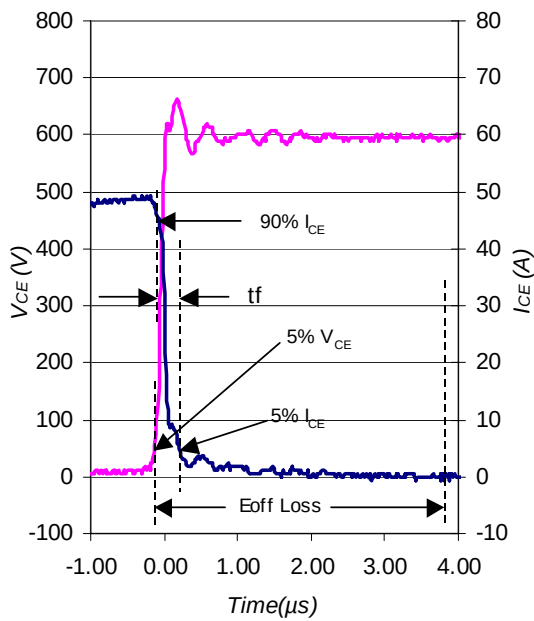


Fig. WF1- Typ. Turn-off Loss Waveform
@ T_J = 125°C using Fig. CT.4

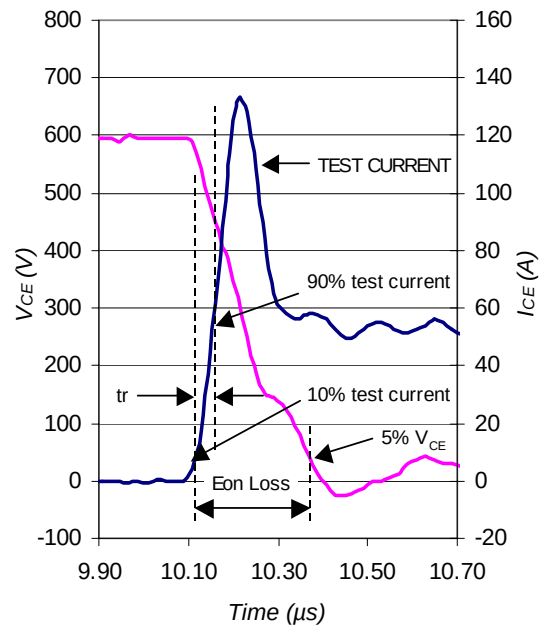
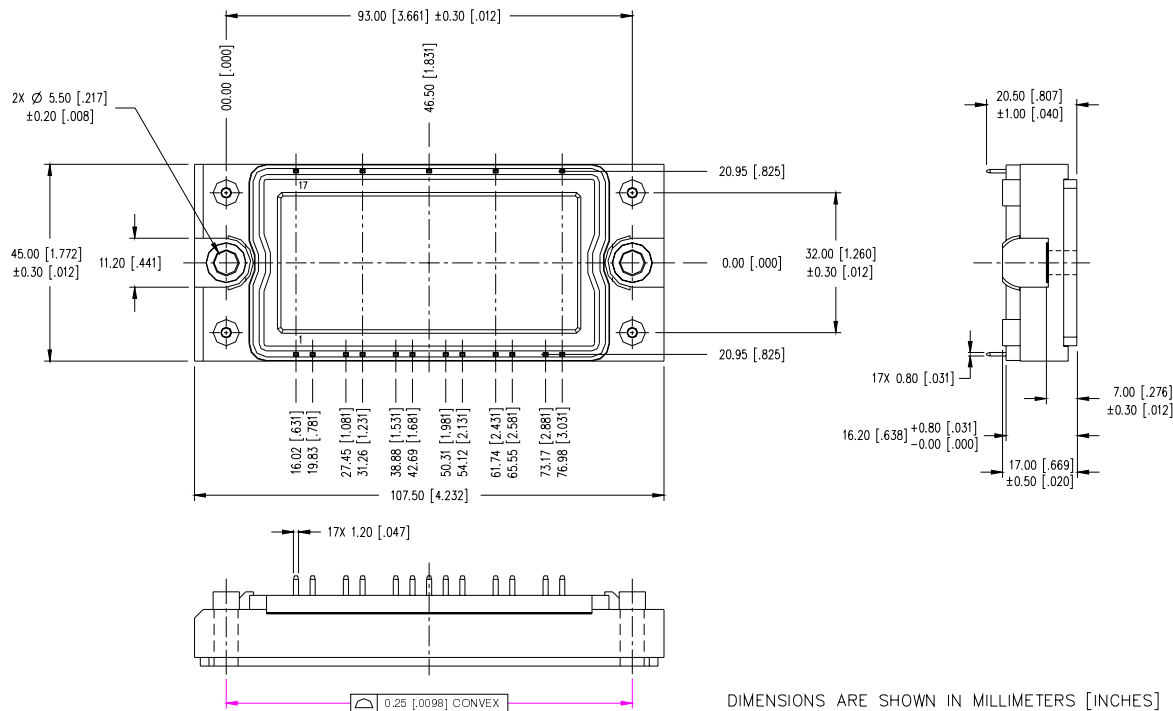


Fig. WF2- Typ. Turn-on Loss Waveform
@ T_J = 125°C using Fig. CT.4

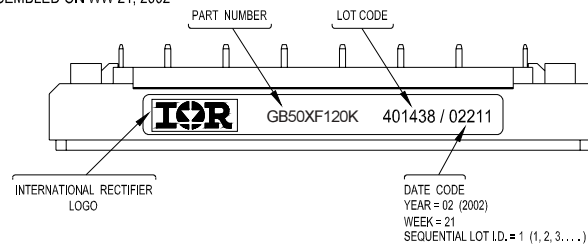
Econo2 6Pak Package Outline

Dimensions are shown in millimeters (inches)



Econo2 6Pak Part Marking Information

EXAMPLE: THIS IS A GB50XF120K
LOT CODE: 401438
ASSEMBLED ON WW 21, 2002



Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

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